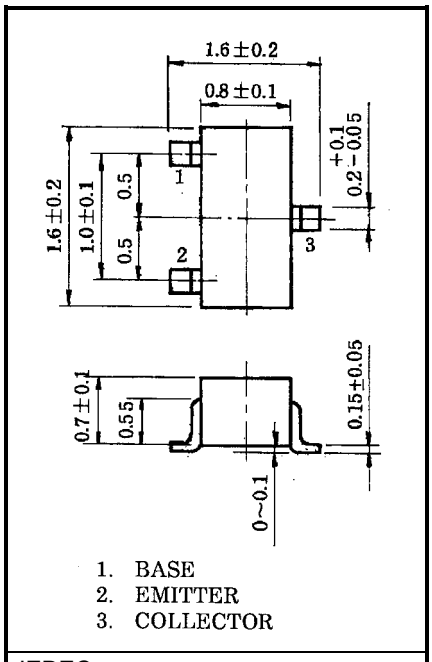
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2107,RN2108,RN2109

Switching, Inverter Circuit, Interface Circuit
and Driver Circuit Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1107~RN1109

Unit: mm

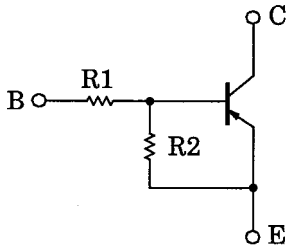


1. BASE
2. EMITTER
3. COLLECTOR

JEDEC	—
EIAJ	—
TOSHIBA	2-2H1A

Weight: 2.4mg

Equivalent Circuit and Bias Resister Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2107	10	47
RN2108	22	47
RN2109	47	22

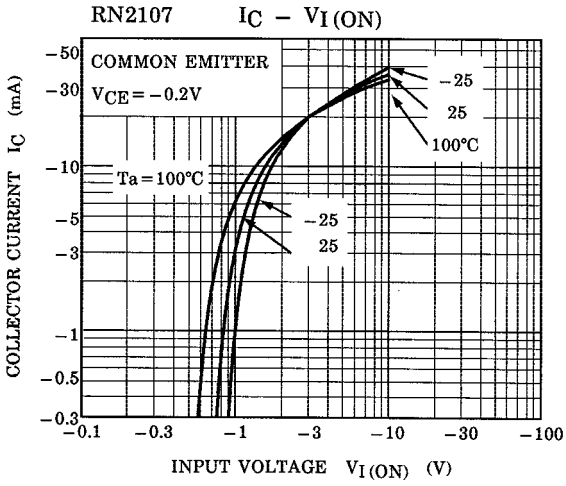
Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

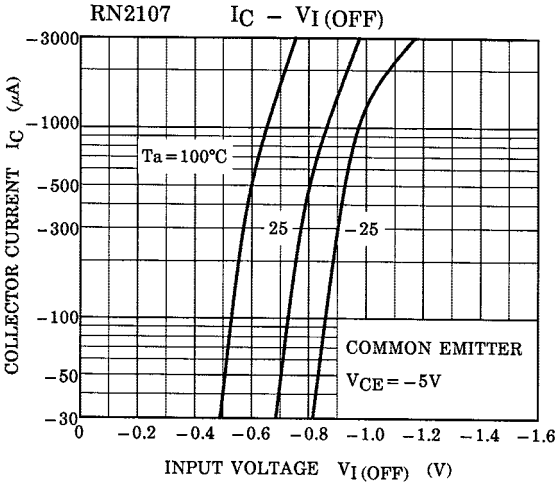
Characteristic		Symbol	Rating	Unit
Collector-base voltage	RN2107~RN2109	V_{CBO}	−50	V
Collector-emitter voltage		V_{CEO}	−50	V
Emitter-base voltage	RN2107	V_{EBO}	−6	V
	RN2108		−7	
	RN2109		−15	
Collector current	RN2107~RN2109	I_C	−100	mA
Collector power dissipation		P_{C*}	100	mW
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	−55~150	°C

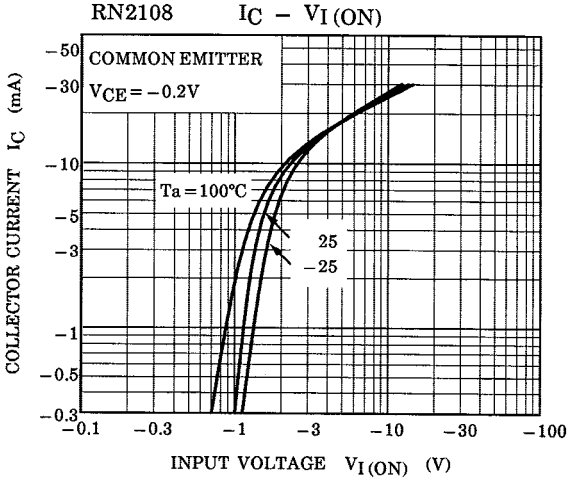
*: Total rating

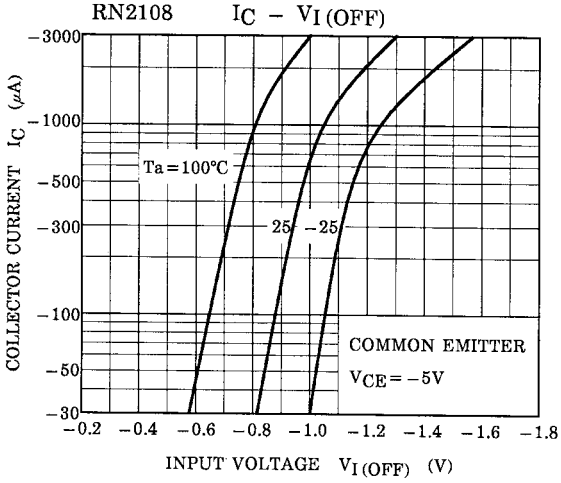
Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

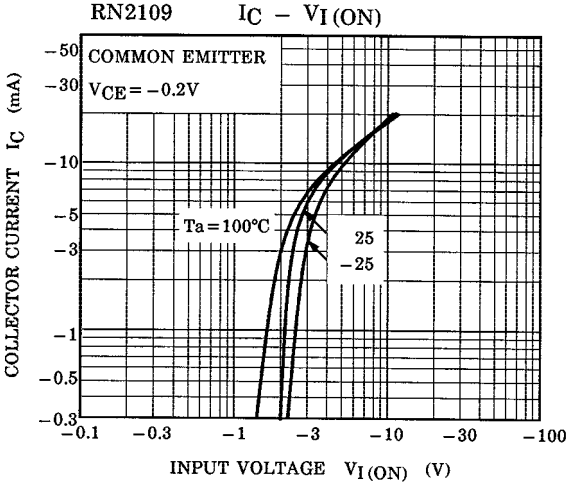
Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2107 ~RN2109	I_{CBO}	—	V_{CB} = −50V, I_E = 0	—	—	−100	nA
		I_{CEO}		V_{CE} = −50V, I_B = 0	—	—	−500	nA
Emitter cut-off current	RN2107	I_{EBO}	—	V_{EB} = −6V, I_C = 0	−0.081	—	−0.15	mA
	RN2108			V_{EB} = −7V, I_C = 0	−0.078	—	−0.145	
	RN2109			V_{EB} = −15V, I_C = 0	−0.167	—	−0.311	
DC current gain	RN2107	h_{FE}	—	V_{CE} = −5V, I_C = −10mA	80	—	—	—
	RN2108				80	—	—	
	RN2109				70	—	—	
Collector-emitter saturation voltage	RN2107 ~RN2109	$V_{CE\ (sat)}$	—	I_C = −5mA, I_B = −0.25mA	—	−0.1	−0.3	V
Input voltage (ON)	RN2107	$V_{I\ (ON)}$	—	V_{CE} = −0.2V, I_C = −5mA	−0.7	—	−1.8	V
	RN2108				−1.0	—	−2.6	
	RN2109				−2.2	—	−5.8	
Input voltage (OFF)	RN2107	$V_{I\ (OFF)}$	—	V_{CE} = −5V, I_C = −0.1mA	−0.5	—	−1.0	V
	RN2108				−0.6	—	−1.16	
	RN2109				−1.5	—	−2.6	
Transition frequency	RN2107 ~RN2109	f_T	—	V_{CE} = −10V, I_C = −5mA	—	200	—	MHz
Collector Output capacitance	RN2107 ~RN2109	C_{ob}	—	V_{CB} = −10V, I_E = 0, f = 1MHz	—	3	6	pF
Input resistor	RN2107	R1	—	—	7	10	13	kΩ
	RN2108				15.4	22	28.6	
	RN2109				32.9	47	61.1	
Resistor ratio	RN2107	R1/R2	—	—	0.191	0.213	0.232	—
	RN2108				0.421	0.468	0.515	
	RN2109				1.92	2.14	2.35	

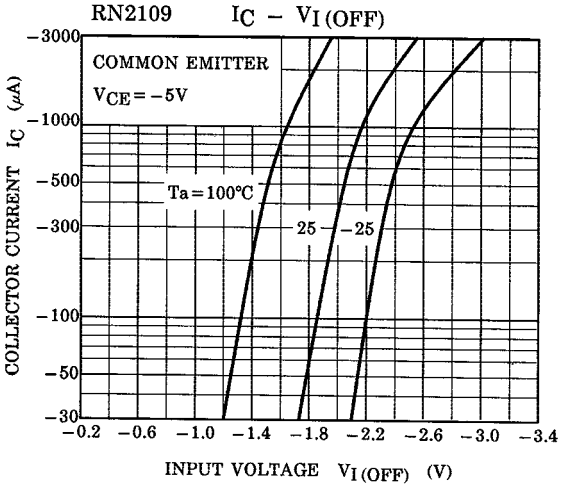

RN2107 IC – VI (ON)
COMMON EMITTER
VCE = –0.2V
Ta = 100°C
–25
25
100°C
–25
25
COLLECTOR CURRENT IC (mA)
INPUT VOLTAGE VI (ON) (V)

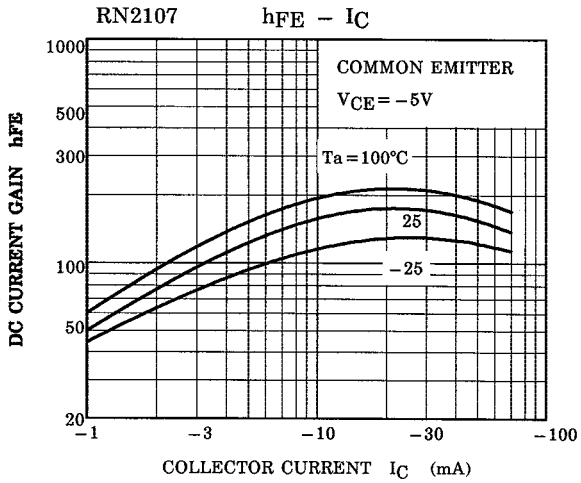

RN2107 IC – VI (OFF)
Ta = 100°C
25
–25
COMMON EMITTER
VCE = –5V
COLLECTOR CURRENT IC (μA)
INPUT VOLTAGE VI (OFF) (V)

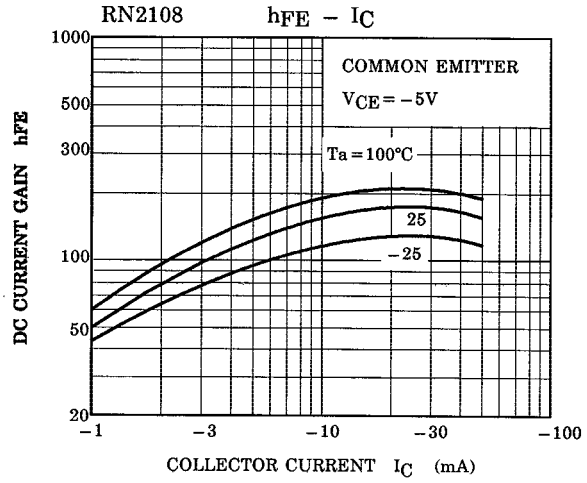

RN2108 IC – VI (ON)
COMMON EMITTER
VCE = –0.2V
Ta = 100°C
25
–25
COLLECTOR CURRENT IC (mA)
INPUT VOLTAGE VI (ON) (V)

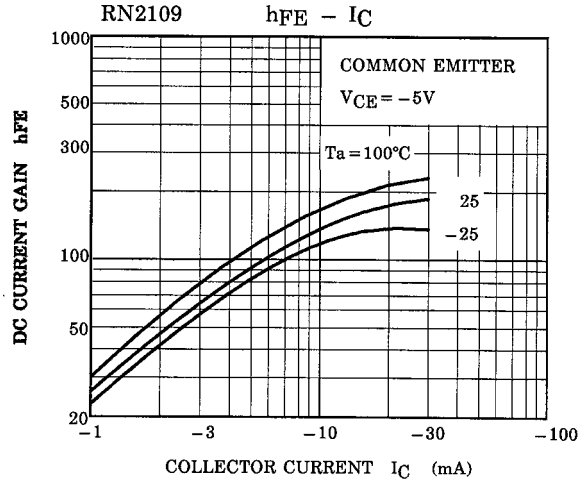

RN2108 IC – VI (OFF)
Ta = 100°C
25
–25
COMMON EMITTER
VCE = –5V
COLLECTOR CURRENT IC (μA)
INPUT VOLTAGE VI (OFF) (V)

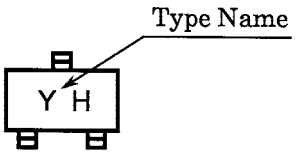
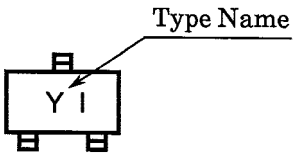
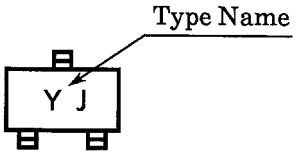

RN2109 IC – VI (ON)
COMMON EMITTER
VCE = –0.2V
Ta = 100°C
25
–25
COLLECTOR CURRENT IC (mA)
INPUT VOLTAGE VI (ON) (V)


RN2109 IC – VI (OFF)
COMMON EMITTER
VCE = –5V
Ta = 100°C
25
–25
COLLECTOR CURRENT IC (μA)
INPUT VOLTAGE VI (OFF) (V)


RN2107
hFE – IC
COMMON EMITTER
VCE = –5V
Ta = 100°C
25
–25
DC CURRENT GAIN hFE
1000
500
300
100
50
20
–1
–3
–10
–30
–100
COLLECTOR CURRENT IC (mA)


RN2108
hFE – IC
COMMON EMITTER
VCE = –5V
Ta = 100°C
25
–25
DC CURRENT GAIN hFE
1000
500
300
100
50
20
–1
–3
–10
–30
–100
COLLECTOR CURRENT IC (mA)


RN2109
hFE – IC
COMMON EMITTER
VCE = –5V
Ta = 100°C
25
–25
DC CURRENT GAIN hFE
1000
500
300
100
50
20
–1
–3
–10
–30
–100
COLLECTOR CURRENT IC (mA)

Type Name	Marking
RN2107	
RN2108	
RN2109	

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